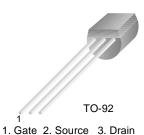


N-Channel RF Amplifier

- This device is designed for HF/VHF mixer/amplifier and applications where process 50is not adequate. Sufficient gain and low noise for sensitive receivers.
- Sourced from process 90.



Absolute Maximum Ratings* Ta=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{DG}	Drain-Gate Voltage	30	V
V _{GS}	Gate-Source Voltage	-30	V
I _{GF}	Forward Gate Current	10	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 ~ 150	°C

* This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These rating are based on a maximum junction temperature of 150 degrees C.
2) These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_a=25°C unless otherwise noted

Parameter	Test Condition	Min.	Max.	Units
teristics				
Gate-Source Breakdwon Voltage	$I_{G} = 1.0 \mu A, V_{DS} = 0$	-30		V
Gate Reverse Current	$V_{GS} = 25V, V_{DS} = 0$		-1.0	nA
Gate-Source Cutoff Voltage	V _{DS} = 15V, I _D = 1.0nA	-1.0	-0.6	V
teristics	•	•	•	•
Zero-Gate Voltage Drain Current *	$V_{DS} = 15V, V_{GS} = 0$	5	15	mA
al Characteristics	•	•	•	•
Forward Transferconductance	V _{GS} = 0V, V _{DS} = 15V, f = 1.0kHz	4500	11000	μmhos
Common- Source Output Conductance	V _{GS} = 0V, V _{DS} = 15V, f = 1.0kHz		50	μmhos
	cteristics Gate-Source Breakdwon Voltage Gate Reverse Current Gate-Source Cutoff Voltage cteristics Zero-Gate Voltage Drain Current * nal Characteristics Forward Transferconductance	trend to the end of th	treatment of the second secon	treisticsGate-Source Breakdwon Voltage $I_G = 1.0\mu A, V_{DS} = 0$ -30Gate Reverse Current $V_{GS} = 25V, V_{DS} = 0$ -1.0Gate-Source Cutoff Voltage $V_{DS} = 15V, I_D = 1.0nA$ -1.0Gate-Source Cutoff Voltage $V_{DS} = 15V, V_{GS} = 0$ 5teristicsZero-Gate Voltage Drain Current * $V_{DS} = 15V, V_{GS} = 0$ 515CharacteristicsForward Transferconductance $V_{GS} = 0V, V_{DS} = 15V, f = 1.0kHz$ 450011000

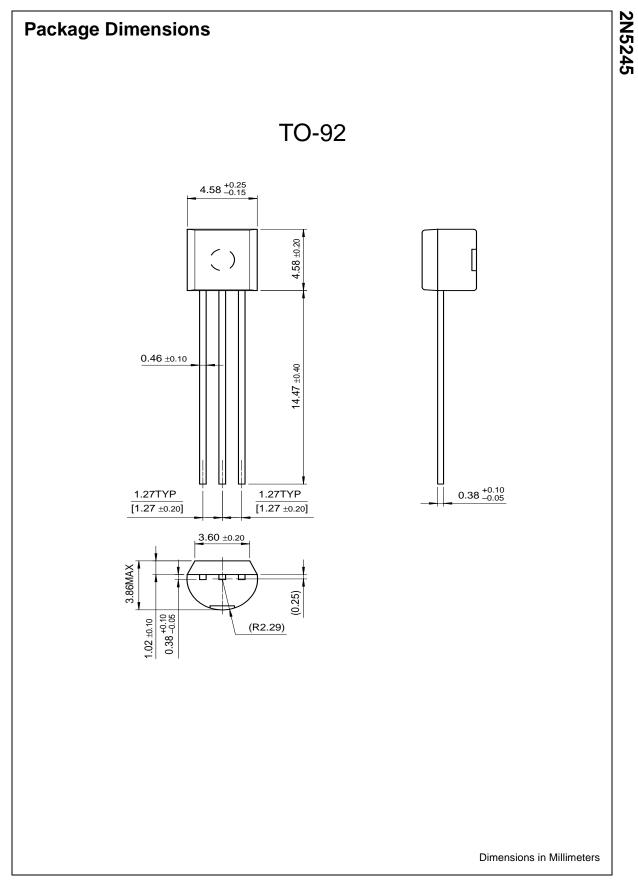
Pulse Test: Pulse ≤ 300µs

Thermal Characteristics Ta=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
PD	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient	357	°C/W

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EnSigna™	ImpliedDisconnect [™]	OCXPro™	SILENT SWITCHER [®]	UltraFET [®]
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The Power Franc	hise™	PACMAN™	Stealth™	
Programmable A	ctive Droop™	POP™	SuperFET™	

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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